2SB1036

Silicon PNP epitaxial planar type

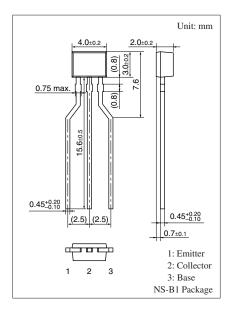
For low-frequency and low-noise amplification

■ Features

- Optimum for high-density mounting
- Allowing supply with the radial taping
- Low noise voltage NV

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-120	V	
Collector-emitter voltage (Base open)	V _{CEO}	-120	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_C	-20	mA	
Peak collector current	I_{CP}	-50	mA	
Collector power dissipation	P _C	300	mW	
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



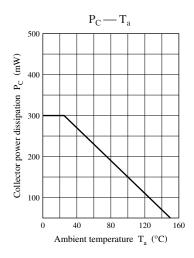
\blacksquare Electrical Characteristics $~T_a = 25^{\circ}C \pm 3^{\circ}C$

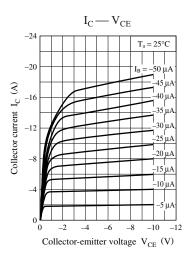
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \ \mu A, I_E = 0$	-120			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-120			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \ \mu A, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-100	nA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			-1	μΑ
Forward current transfer ratio *	h_{FE}	$V_{CE} = -5 \text{ V}, I_{C} = -2 \text{ mA}$	180		520	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$			- 0.6	V
Transition frequency	f_T	$V_{CB} = -5 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CE} = -40 \text{ V}, I_{C} = -1 \text{ mA}, G_{V} = 80 \text{ dB}$			150	mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

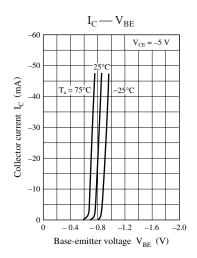
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

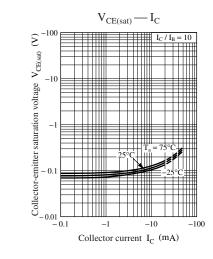
2. *: Rank classification

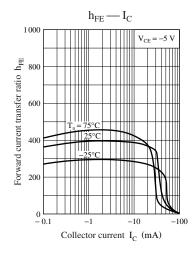
Rank	R	S
h_{FE}	180 to 360	260 to 520

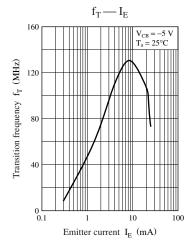


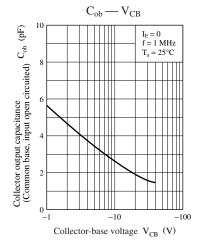


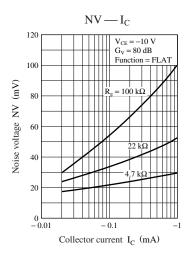












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